CLAIM AMENDMENTS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-6 (canceled)

Claim 7 (currently amended): A device for protecting an electronic module ~~(μC, C-T, T2)~~ disposed in a control device ~~(ST)~~ in a multi-voltage on-board electrical system ~~(12V/42V)~~ having an accumulator ~~(BAT1)~~ with a low on-board electrical system voltage ~~(Vbat1)~~ against short circuiting to a high on-board electrical system voltage, comprising:

a MOSFET transistor ~~(T1)~~ having a drain source path ~~(D-S)~~ inserted between a control device connection ~~(A, A1, A2)~~ and a connection ~~(E, E1, E2)~~ of the electronic module ~~(μC, C-T, T2)~~, and with:

a source ~~(S)~~ connected to the connection ~~(E, E1, E2)~~ of the electronic module ~~(μC, C-T, T2)~~;

a drain ~~(D)~~ connected to the control device connection ~~(A, A1, A2)~~; and

a gate ~~(G)~~;

a Zener diode ~~(D1)~~ connected between said gate ~~(G)~~ and said source ~~(S)~~ of said MOSFET transistor ~~(T1)~~;

a gate resistor ~~(Rv)~~ connected between said gate ~~(G)~~ of said MOSFET transistor ~~(T1)~~ and a positive pole ~~(+Vbat1)~~ of the first accumulator ~~(BAT1)~~; and

a diode ~~(D2)~~ connected in parallel with said gate resistor ~~(Rv)~~, for conducting current in a direction from said gate ~~(G)~~ to the positive pole ~~(+Vbat1)~~ of the accumulator ~~(Bat1)~~;

wherein when a short circuit to the high on board electrical system voltage is conducted to said drain, said MOSFET transistor turns on or remains turned on.

Claim 8 (currently amended): The device according to claim 7, wherein said electronic module is disposed in control device ~~(ST)~~ for controlling low-power consumers or for processing/transmitting data.

Claim 9 (currently amended): The device according to claim 7, wherein said Zener diode ~~(D1)~~ is configured with a breakdown voltage ~~(Vz)~~ lower than a maximum permitted gate source voltage ~~(Vgs)~~ of said MOSFET transistor ~~(T1)~~.

Claim 10 (currently amended): The device according to claim 7, wherein said MOSFET transistor ~~(T1)~~ has a threshold voltage ~~(Vth)~~ and, in an event of a short circuit to a highest voltage of the on-board electrical system active at the device connection ~~(A, A1, A2)~~, a source voltage ~~(Vs)~~ of said transistor ~~(T1)~~ is limited to a value Vs = Vbat1 – Vth, where Vs is the source voltage, Vbat1 is

the low on-board voltage ~~(Vbat1)~~, and Vth is the threshold voltage of said transistor ~~(T1)~~.

Claim 11 (currently amended). The device according to claim 7, wherein, on occurrence of a short circuit to a highest voltage of the on-board electrical system active at the device connection ~~(A, A1, A2)~~, said diode ~~(D2)~~ connected in parallel to said gate resistor ~~(Rv)~~ limits the gate voltage ~~(Vg)~~ of said MOSFET transistor ~~(T1)~~ to a value Vg = Vbat1 + Vd, wherein Vg is the gate voltage, Vbat1 is the low on-board voltage ~~(Vbat1)~~, and Vd is a conducting state voltage ~~(Vd)~~ of said diode ~~(D2)~~.

Claim 12 (currently amended): The device according to claim 7, with the protective circuit ~~(Ss, Ssa, Ssb)~~ integrated in an ASIC.

Claim 13 (original): The device according to claim 7, wherein the multi-voltage on-board electrical system is a motor vehicle on-board electrical system.